

**2SC5296**

Ultrahigh-Definition CRT Display Horizontal Deflection Output Applications

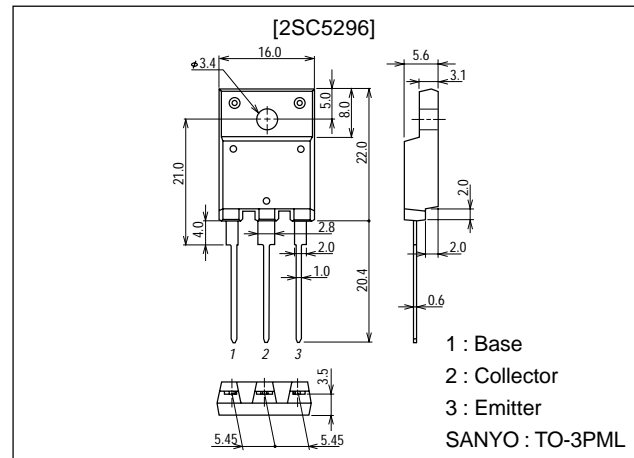
Features

- High speed : $t_f=100\text{ns}$ typ.
- High breakdown voltage : $V_{CBO}=1500\text{V}$.
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.
- On-chip damper diode.

Package Dimensions

unit:mm

2039D



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		1500	V
Collector-to-Emitter Voltage	V_{CEO}		800	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		8	A
Collector Current (Pulse)	I_{CP}		16	A
Collector Dissipation	P_C		3.0	W
		$T_c=25^\circ\text{C}$	60	W
Junction Temperature	T_j		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=800\text{V}, I_E=0$			10	μA
	I_{CES}	$V_{CE}=1500\text{V}, R_{BE}=0$			1.0	mA
Collector-to-Emitter Sustain Voltage	$V_{CEO(sus)}$	$I_C=100\text{mA}, I_B=0$	800			V
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$	40		130	mA
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=5\text{A}, I_B=1.25\text{A}$			5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=5\text{A}, I_B=1.25\text{A}$			1.5	V

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■ Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
DC Current Gain	h_{FE1}	$V_{CE}=5V, I_C=1A$	15		25	
	h_{FE2}	$V_{CE}=5V, I_C=5A$	4		7	
Storage Time	t_{stg}	$I_C=4A, I_{B1}=0.8A, I_{B2}=-1.6A$			3.0	μs
Fall Time	t_f	$I_C=4A, I_{B1}=0.8A, I_{B2}=-1.6A$		0.1	0.2	μs

Switching Time Test Circuit

